

FEB 13 2003

PTO/SB/08A (10-01)

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**Complete if Known****INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Sheet

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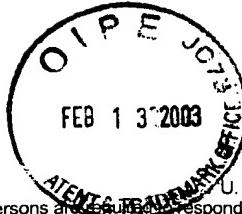
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		<b>Complete if Known</b>	
		Application Number	09/853,233
		Filing Date	May 11, 2001
		First Named Inventor	Steven T. Harshfield
		Art Unit	2823
		Examiner Name	William D. Coleman
		Attorney Docket Number	M4065.0743/P743

**U. S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
AA	2002/0000666	1/3/2002	Kozicki et al.		
AB	2002/0168820 App.	11/2002	Kozicki		
AC	2000/0072188 App	6/2002	Gilton		
AD	2002/0123169 App	9/2002	Moore et al.		
AE	2002/0123248 App.	9/2002	Moore et al.		
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AH	4,269,935	5/1981	Masters et al.		
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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	2	of	10	Attorney Docket Number	M4065.0743/P743
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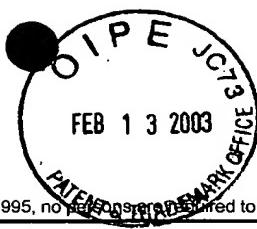
### FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
BA	JP 56126916 A		10/19981	Akira et al.		
BB	WO 02/21542		03/14/2002	Kozicki et al.		
BC	WO 00/48196		08/17/2000	Kozicki et al.		
BD	WO 97/48032		12/18/1997	Kozicki et al.		
BE	WO 99/28914		06/10/1999	Kozicki et al.		

Examiner Signature	Date Considered
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See attached Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.



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Substitute for form 1449B/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				Application Number	09/853,233
Sheet	3	of	10	Filing Date	May 11, 2001
				First Named Inventor	Steven T. Harshfield
				Group Art Unit	2823
				Examiner Name	William D. Coleman
				Attorney Docket Number	M4065.0743/P473

<b>OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS</b>			
Examiner Initials'	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
	CA	Abdel-All, A.; Elshafie,A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge5As38Te57 chalcogenide glass, Vacuum 59 (2000) 845-853.	T <sup>2</sup>
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se75Ge25-xSbx, Appl. Phys. A 55 (1992) 167-169.	
	CE	Afifi,M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe1-x, Egypt, J. Phys. 17 (1986) 335-342.	
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	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
	CL	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: Programmable Metalization Cell(PMC), pp. 1-6 (Pre-May 2000).	
	CM	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.	
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	CR	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.	
	CS	Bernede, J.C., Switching and silver movements in Ag <sub>2</sub> Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.	
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C I P E J C T

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				First Named Inventor	Steven T. Harshfield
				Group Art Unit	2823
				Examiner Name	William D. Coleman
Sheet	4	of	10	Attorney Docket Number	M4065.0743/P473

CW	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg4I5, Solid State Ionics 70/71 (1994) 72-76.
CX	Boolchand, P., The maximum in glass transition temperature (Tg) near x=1/3 in GexSe1-x Glasses, Asian Journal of Physics (2000) 9, 709-72.
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CB1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.
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CL1	Chen, C.H.; Tai, K.L., Whisker growth induced by Ag photodoping in glassy GexSe1-x films, Appl. Phys. Lett. 37 (1980) 1075-1077.
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				Group Art Unit	2823
				Examiner Name	William D. Coleman
Sheet	5	of	10	Attorney Docket Number	M4065.0743/P473

CU1	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.	
CV1	Drusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.	
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CX1	Ei Gharras, Z.; Bourahla, A.; Vautier, C., Role of photoinduced defects in amorphous Ge <sub>x</sub> Se <sub>1-x</sub> photoconductivity, J. Non-Cryst. Solids 155 (1993) 171-179.	
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CA2	Ei-kady, Y.L., The threshold switching in semiconducting glass Ge <sub>21</sub> Se <sub>17</sub> Te <sub>62</sub> , Indian J. Phys. 70A (1996) 507-516.	
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CJ2	Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe <sub>2</sub> thin films, Phys. Rev. B 38 (1988) 12388-12403.	
CK2	Fleury, G.; Hamou, A.; Viger, C.; Vautier, C., Conductivity and crystallization of amorphous selenium, Phys. Stat. Sol. (a) 64 (1981) 311-316.	
CL2	Fritzsche, H., Optical and electrical energy gaps in amorphous semiconductors, J. Non-Cryst. Solids 6 (1971) 49-71.	
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Steven T. Harshfield

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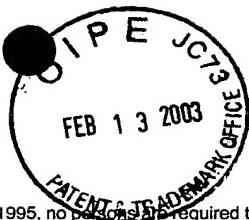
Examiner Name

William D. Coleman

Attorney Docket Number

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	1545-52.	
CR2	Gupta, Y.P., On electrical switching and memory effects in amorphous chalcogenides, J. Non-Cryst. Sol. 3 (1970) 148-154.	
CS2	Haberland, D.R.; Stiegler, H., New experiments on the charge-controlled switching effect in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 408-414.	
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CY2	Hayashi, T.; Ono, Y.; Fukaya, M.; Kan, H., Polarized memory switching in amorphous Se film, Japan. J. Appl. Phys. 13 (1974) 1163-1164.	
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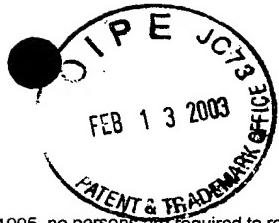
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				Filing Date	May 11, 2001
				First Named Inventor	Steven T. Harshfield
				Group Art Unit	2823
				Examiner Name	William D. Coleman
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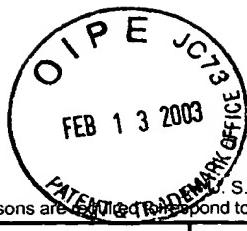
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Group Art Unit	2823
Examiner Name	William D. Coleman

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